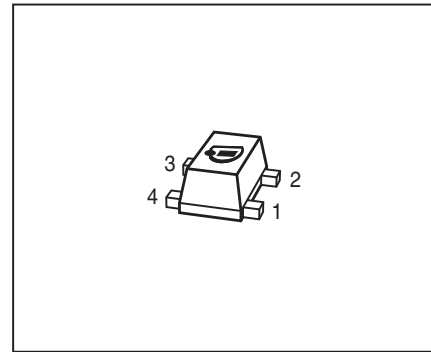


Low Noise Silicon Bipolar RF Transistor

- For low current applications
- Minimum noise figure $NF_{\min} = 1.25$ dB at 1.8 GHz
Outstanding $G_{\text{ms}} = 22.5$ dB at 1.8 GHz
- Transition frequency $f_T = 25$ GHz
- Pb-free (RoHS compliant) and halogen-free thin small flat package (1.4 x 0.8 x 0.59 mm) with visible leads
- Qualification report according to AEC-Q101 available



ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Type	Marking	Pin Configuration						Package
BFP405F	ALs	1=B	2=E	3=C	4=E	-	-	TSFP-4

Maximum Ratings at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage $T_A = 25$ °C $T_A = -55$ °C	V_{CEO}	4.5 4.1	V
Collector-emitter voltage	V_{CES}	15	
Collector-base voltage	V_{CBO}	15	
Emitter-base voltage	V_{EBO}	1.5	
Collector current	I_C	25	mA
Base current	I_B	3	
Total power dissipation ¹⁾ $T_S \leq 112$ °C	P_{tot}	75	mW
Junction temperature	T_J	150	°C
Storage temperature	T_{Stg}	-55 ... 150	

¹⁾ T_S is measured on the emitter lead at the soldering point to the pcb

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}	500	K/W

Electrical Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 1\text{ mA}, I_B = 0$	$V_{(BR)CEO}$	4	5	-	V
Collector-emitter cutoff current $V_{CE} = 15\text{ V}, V_{BE} = 0$	I_{CES}	-	-	10	μA
Collector-base cutoff current $V_{CB} = 5\text{ V}, I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 0.5\text{ V}, I_C = 0$	I_{EBO}	-	-	1	μA
DC current gain $I_C = 5\text{ mA}, V_{CE} = 4\text{ V}$, pulse measured	h_{FE}	60	95	130	-

¹For the definition of R_{thJS} please refer to Application Note AN077 (Thermal Resistance Calculation)

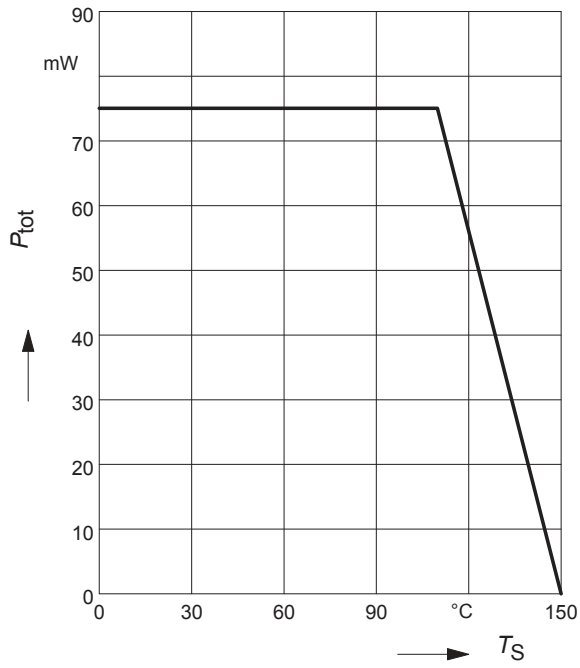
Electrical Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Transition frequency $I_C = 10\text{ mA}$, $V_{CE} = 3\text{ V}$, $f = 2\text{ GHz}$	f_T	18	25	-	GHz
Collector-base capacitance $V_{CB} = 2\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, emitter grounded	C_{cb}	-	0.05	0.1	pF
Collector emitter capacitance $V_{CE} = 2\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, base grounded	C_{ce}	-	0.2	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$, $V_{CB} = 0$, collector grounded	C_{eb}	-	0.25	-	
Minimum noise figure $I_C = 2\text{ mA}$, $V_{CE} = 2\text{ V}$, $f = 1.8\text{ GHz}$, $Z_S = Z_{Sopt}$	NF_{min}	-	1.25	-	dB
Power gain, maximum stable ¹⁾ $I_C = 5\text{ mA}$, $V_{CE} = 2\text{ V}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, $f = 1.8\text{ GHz}$	G_{ms}	-	22.5	-	dB
Insertion power gain $V_{CE} = 2\text{ V}$, $I_C = 5\text{ mA}$, $f = 1.8\text{ GHz}$, $Z_S = Z_L = 50\text{ }\Omega$	$ S_{21} ^2$	-	18	-	
Third order intercept point at output ²⁾ $V_{CE} = 2\text{ V}$, $I_C = 5\text{ mA}$, $f = 1.8\text{ GHz}$, $Z_S = Z_L = 50\text{ }\Omega$	$IP3$	-	14	-	dBm
1dB compression point at output $I_C = 5\text{ mA}$, $V_{CE} = 2\text{ V}$, $Z_S = Z_L = 50\text{ }\Omega$, $f = 1.8\text{ GHz}$	P_{-1dB}	-	0	-	

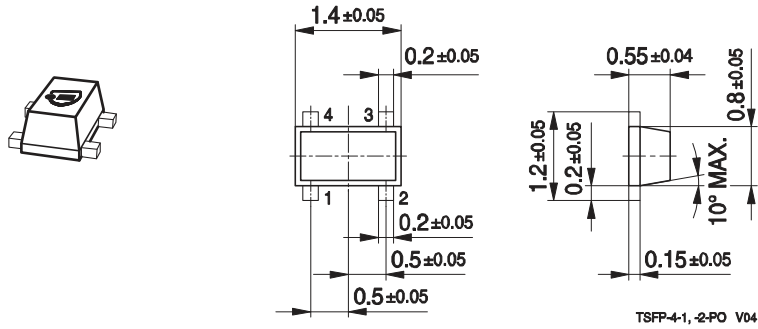
$$^1G_{ms} = |S_{21} / S_{12}|$$

²IP3 value depends on termination of all intermodulation frequency components.
Termination used for this measurement is 50Ω from 0.1 MHz to 6 GHz

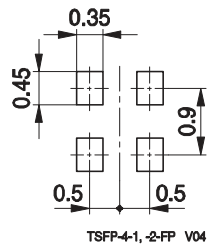
Total power dissipation $P_{\text{tot}} = f(T_S)$



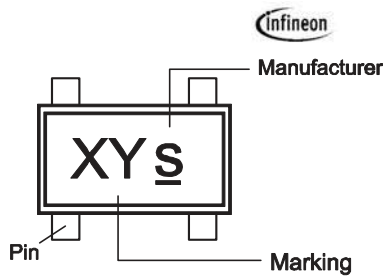
Package Outline



Foot Print

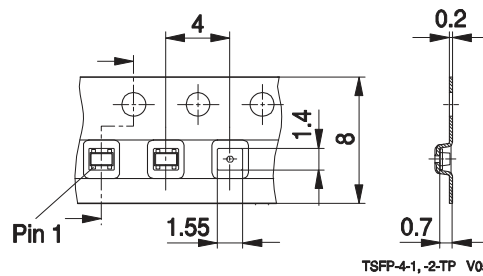


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
 Reel ø330 mm = 10.000 Pieces/Reel



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